





#### 400V NPN MEDIUM POWER TRANSISTOR IN SOT223

#### **Features**

- BV<sub>CEO</sub> > 400V
- I<sub>C</sub> = 300mA High Continuous Current
- Excellent h<sub>FE</sub> Characteristics up to 100mA
- Low Saturation Voltage V<sub>CE(sat)</sub> < 200mV @ 20mA</li>
- Complementary PNP Type: FZT558
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

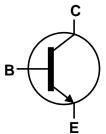
#### **Mechanical Data**

- Case: SOT223
- Case Material: Molded Plastic. "Green" Molding Compound;
- UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208®3
- Weight: 0.112 grams (Approximate)

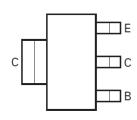




Top View



Device Symbol



Top View Pin-Out

#### Ordering Information (Notes 4 & 5)

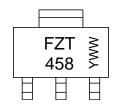
Product	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
FZT458TA	AEC-Q101	FZT458	7	12	1,000
FZT458QTA	Automotive	FZT458	7	12	1,000

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified.
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

#### **Marking Information**

SOT223



FZT 458 = Product Type Marking Code YWW = Date Code Marking Y or  $\overline{Y}$  = Last Digit of Year (ex: 5= 2015) WW or  $\overline{W}W$  = Week Code (01~53)





### Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	400	V
Collector-Emitter Voltage	V <sub>CEO</sub>	400	V
Emitter-Base Voltage	V <sub>EBO</sub>	7	V
Continuous Collector Current	Ic	300	mA
Base Current	I <sub>B</sub>	200	mA
Peak Pulse Current	I <sub>CM</sub>	1	А

### Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Dawar Dissination	(Note 6)		2	W
Power Dissipation	(Note 7)	P <sub>D</sub>	3	W
Thermal Resistance, Junction to Ambient	(Note 6)	D	62.5	°C/W
Thermal Resistance, Junction to Ambient	(Note 7)	− R <sub>θJA</sub>	41.7	°C/W
Thermal Resistance, Junction to Leads (Note 8	$R_{\theta JL}$	19.41	°C/W	
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C	

# ESD Ratings (Note 9)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	8,000	V	3B
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

- 6. For a device mounted with the collector lead on 25mm x 25mm 2oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
- 7. Same as Note 6, except the device is mounted on 50mm x 50mm single sided 2oz weight copper.

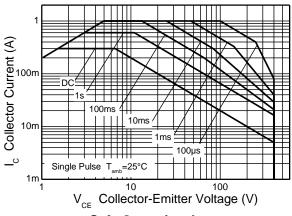
  8. Thermal resistance from junction to solder-point (at the end of the collector lead).

  9. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

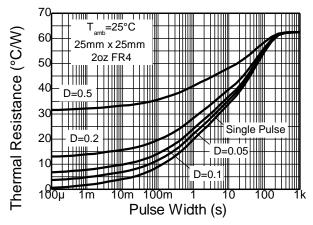




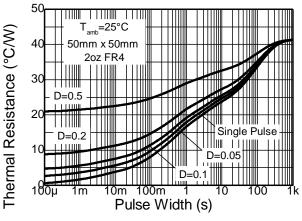
# **Thermal Characteristics and Derating Characteristics**



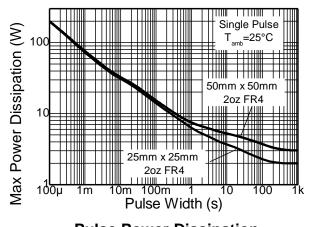
**Safe Operating Area** 



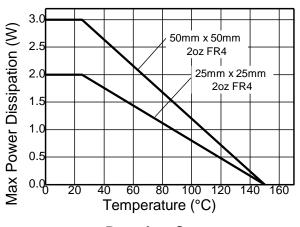
**Transient Thermal Impedance** 



**Transient Thermal Impedance** 



**Pulse Power Dissipation** 



**Derating Curve** 





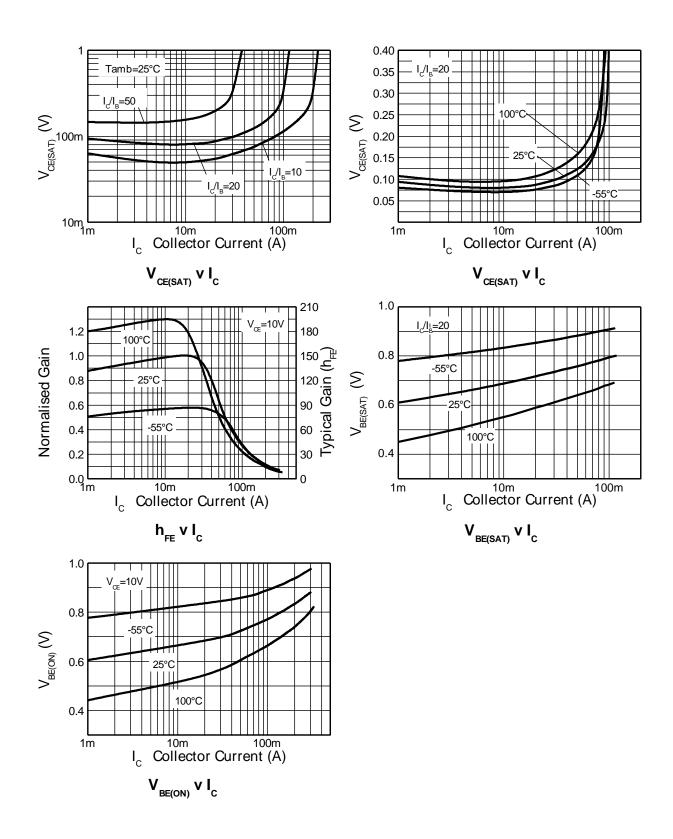
# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	400	-	-	V	$I_{C} = 100 \mu A$
Collector-Emitter Breakdown Voltage (Note 10)	BV <sub>CEO</sub>	400	-	-	V	$I_C = 10mA$
Emitter-Base Breakdown Voltage	$BV_{EBO}$	7	-	-	V	$I_E = 100\mu A$
Collector Cut-Off Current	I <sub>CBO</sub>	-	-	100	nA	V <sub>CB</sub> = 320V
Collector Cut-Off Current	I <sub>CES</sub>	-	-	100	nA	V <sub>CE</sub> = 320V
Emitter Cut-Off Current	I <sub>EBO</sub>	-	_	100	nA	$V_{EB} = 4V$
Collector-Emitter Saturation Voltage (Note 10)	V <sub>CE(sat)</sub>	-	-	0.2	V	$I_C = 20mA$ , $I_B = 2mA$
Collector-Emitter Saturation Voltage (Note 10)		_	_	0.5		$I_C = 50$ mA, $I_B = 6$ mA
Base-Emitter Saturation Voltage (Note 10)	V <sub>BE(sat)</sub>	-	_	0.9	V	$I_C = 50$ mA, $I_B = 5$ mA
Base-Emitter Turn-On Voltage (Note 10)	$V_{BE(on)}$	-	_	0.9	V	$I_C = 50 \text{mA}, V_{CE} = 10 \text{V}$
		100	_	_		$I_C = 1mA$ , $V_{CE} = 10V$
DC Current Gain (Note 10)	h <sub>FE</sub>	100	_	300		$I_C = 50 \text{mA}, V_{CE} = 10 \text{V}$
		15	_	_		$I_C = 100 \text{mA}, V_{CE} = 10 \text{V}$
Current Gain-Bandwidth Product (Note 10)	f⊤	50	_	-	MHz	$V_{CE} = 20V$ , $I_C = 10mA$ f = 20MHz
Output Capacitance (Note 10)	$C_obo$	-	_	5	pF	$V_{CB} = 20V. f = 1MHz$
Switching Times	ton		135	_	ns	$I_C = 50 \text{mA}, V_{CC} = 100 \text{V}$
Switching Times	t <sub>off</sub>	_	2260	_	115	$I_{B1} = 5mA, I_{B2} = -10mA$

Note: 10. Measured under pulsed conditions. Pulse width  $\leq$  300 $\mu$ s. Duty cycle  $\leq$  2%.



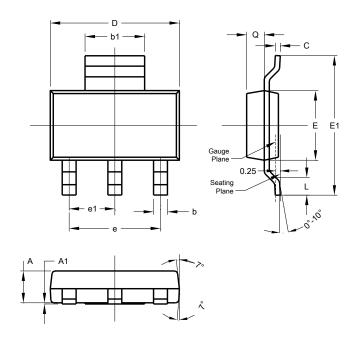
### Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)





### **Package Outline Dimensions**

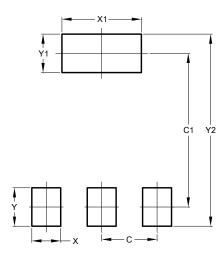
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SOT223					
Dim	Min	Max	Тур		
Α	1.55	1.65	1.60		
A1	0.010	0.15	0.05		
b	0.60	0.80	0.70		
b1	2.90	3.10	3.00		
С	0.20	0.30	0.25		
D	6.45	6.55	6.50		
Е	3.45	3.55	3.50		
E1	6.90	7.10	7.00		
е	-	-	4.60		
e1	-	-	2.30		
L	0.85	1.05	0.95		
Q	0.84	0.94	0.89		
All Dimensions in mm					

# **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	2.30
C1	6.40
Х	1.20
X1	3.30
Y	1.60
Y1	1.60
Y2	8.00

Note: For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device terminals and PCB tracking.





May 2015

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